

METHOD FOR FORMING A SEMICONDUCTOR DEVICE HAVING
METAL SILICIDE

5

Abstract of the Disclosure

In one embodiment, a top surface of a semiconductor device (18) is amorphized in a tool (1). A metal is deposited over the semiconductor substrate using the same tool. In one embodiment, the same chambers are used. In an embodiment, the tool is a sputtering tool, such as a physical vapor
10 deposition (PVD). The semiconductor substrate may be annealed to form a metal silicide (122) over at least a portion of the semiconductor device that includes silicon.